Akinobu Teramoto

List of Publications by Year
in descending order

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274	2,257	331538 21	395590 33
papers	citations	h-index	g-index

276	276	276	1180
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Adsorption and surface reaction of isopropyl alcohol on SiO₂ surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 053201.	0.9	0
2	Impact on the Conductance Method of the Asymmetry in the AC Response Induced by Interface Trap Levels. ECS Journal of Solid State Science and Technology, 2021, 10, 043004.	0.9	0
3	A high-precision current measurement platform applied for statistical measurement of discharge current transient spectroscopy of traps in SiN dielectrics. Japanese Journal of Applied Physics, 2021, 60, 086501.	0.8	0
4	Evaluation of Low-Frequency Noise in MOSFETs Used as a Key Component in Semiconductor Memory Devices. Electronics (Switzerland), 2021, 10, 1759.	1.8	7
5	Plasma resistance of sintered and ion-plated yttrium oxyfluorides with various Y, O, and F composition ratios for use in plasma process chamber. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	5
6	Study on Influence of O2 Concentration in Wafer Cleaning Ambient for Smoothness of Silicon (110) Surface Appearing at Sidewall of Three-Dimensional Transistors. ECS Transactions, 2020, 97, 23-29.	0.3	0
7	Resistance Measurement Platform for Statistical Analysis of Emerging Memory Materials. IEEE Transactions on Semiconductor Manufacturing, 2020, 33, 232-239.	1.4	2
8	Influence of silicon wafer surface roughness on semiconductor device characteristics. Japanese Journal of Applied Physics, 2020, 59, SMMB06.	0.8	13
9	Effect of Drain-to-Source Voltage on Random Telegraph Noise Based on Statistical Analysis of MOSFETs with Various Gate Shapes. , 2020, , .		3
10	High reliability CoFeB/MgO/CoFeB magnetic tunnel junction fabrication using low-damage ion beam etching. Japanese Journal of Applied Physics, 2020, 59, SGGB05.	0.8	2
11	Control of ion-flux and ion-energy in direct inductively coupled plasma reactor for interfacial-mixing plasma-enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 032408.	0.9	4
12	A high-precision 1 Î©â€“10 MÎ© range resistance measurement platform for statistical evaluation of emerging memory materials. Japanese Journal of Applied Physics, 2020, 59, SGGL03.	0.8	1
13	Impact of CoFeB surface roughness on reliability of MgO films in CoFeB/MgO/CoFeB magnetic tunnel junction. Japanese Journal of Applied Physics, 2019, 58, SIIB29.	0.8	3
14	SiNx Deposition at Low Temperature Using UV-Irradiated NH3. ECS Transactions, 2019, 89, 31-36.	0.3	0
15	Resistance Measurement Platform for Statistical Analysis of Next Generation Memory Materials. , 2019, , .		3
16	Low-Temperature Deposition of Silicon Nitride Films Using Ultraviolet-Irradiated Ammonia. ECS Journal of Solid State Science and Technology, 2019, 8, P715-P718.	0.9	0
17	Monte Carlo Simulation of Nanowires Array Biosensor With AC Electroosmosis. IEEE Transactions on Electron Devices, 2018, 65, 1932-1938.	1.6	2
18	Experimental investigation of localized stress-induced leakage current distribution in gate dielectrics using array test circuit. Japanese Journal of Applied Physics, 2018, 57, 04FE11.	0.8	0

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19	An Electrical Impedance Biosensor Array for Tracking Moving Cells. , 2018, , .		2
20	Effect of drain current on appearance probability and amplitude of random telegraph noise in low-noise CMOS image sensors. Japanese Journal of Applied Physics, 2018, 57, 04FF08.	0.8	4
21	Statistical Analysis of Threshold Voltage Variation Using MOSFETs With Asymmetric Source and Drain. IEEE Electron Device Letters, 2018, 39, 1836-1839.	2.2	2
22	Reliability of MgO in magnetic tunnel junctions formed by MgO sputtering and Mg oxidation. , 2018, , .		1
23	[Papers] Statistical Analyses of Random Telegraph Noise in Pixel Source Follower with Various Gate Shapes in CMOS Image Sensor. ITE Transactions on Media Technology and Applications, 2018, 6, 163-170.	0.3	5
24	[Papers] Impacts of Random Telegraph Noise with Various Time Constants and Number of States in Temporal Noise of CMOS Image Sensors. ITE Transactions on Media Technology and Applications, 2018, 6, 171-179.	0.3	4
25	Stable yttrium oxyfluoride used in plasma process chamber. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	0.9	29
26	Performances of accumulation-mode n- and p-MOSFETs on Si(110) wafers. Japanese Journal of Applied Physics, 2017, 56, 04CD15.	0.8	5
27	Formation technology of flat surface with epitaxial growth on ion-implanted (100)-oriented Si surface of thin silicon-on-insulator. Japanese Journal of Applied Physics, 2017, 56, 105503.	0.8	0
28	Atomically flat interface for noise reduction in SOI-MOSFETs. , 2017, , .		0
29	Hole-Trapping Process at Al2O3/GaN Interface Formed by Atomic Layer Deposition. IEEE Electron Device Letters, 2017, 38, 1309-1312.	2.2	4
30	Impact of SiO<inf>2</inf>/Si interface micro-roughness on SILC distribution and dielectric breakdown: A comparative study with atomically flattened devices. , 2017, , .		3
31	Monte-Carlo simulation of biomolecules' fluid-dynamics in electrolyte facing nanowires biosensor. , 2017, , .		2
32	Introduction of Atomically Flattening of Si Surface to Large-Scale Integration Process Employing Shallow Trench Isolation. ECS Journal of Solid State Science and Technology, 2016, 5, P67-P72.	0.9	5
33	Effects of Oxygen Microbubbles on Photoresist Layers under Hot Water Conditions. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2016, 29, 643-646.	0.1	2
34	Detection of short range order in SiO2 thin-films by grazing-incidence wide and small-angle X-ray scattering. Journal of Applied Physics, 2016, 119, 154103.	1.1	1
35	Proposal of tunneling- and diffusion-current hybrid MOSFET: A device simulation study. Japanese Journal of Applied Physics, 2016, 55, 04ED12.	0.8	1
36	Impact of doping concentration on 1/f noise performances of accumulation-mode Si(100) n-MOSFETs. Japanese Journal of Applied Physics, 2016, 55, 04ED08.	0.8	3

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37	Oxidizing Species Dependence of the Interface Reaction during Atomic-Layer-Deposition Process and Post-Deposition-Anneal. ECS Transactions, 2016, 75, 207-214.	0.3	1
38	Evaluating Work-Function and Composition of ErSixon Various Surface Orientation of Silicon. ECS Journal of Solid State Science and Technology, 2016, 5, P608-P613.	0.9	1
39	Low Leakage Current Al2O3 Metal-Insulator-Metal Capacitors Formed By Atomic Layer Deposition at Optimized Process Temperature and O2 Post Deposition Annealing. ECS Transactions, 2016, 72, 91-100.	0.3	12
40	Introduction of a High Selectivity Etching Process with Advanced SiNx Etch Gas in the Fabrication of FinFET Structures. ECS Transactions, 2016, 72, 23-30.	0.3	1
41	Random telegraph noise measurement and analysis based on arrayed test circuit toward high S/N CMOS image sensors. , 2016, , .		12
42	Low Interface Trap Density and High Breakdown Electric Field SiN Films on GaN Formed by Plasma Pretreatment Using Microwave-Excited Plasma-Enhanced Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2016, 63, 1795-1801.	1.6	6
43	Atomically flattening of Si surface of silicon on insulator and isolation-patterned wafers. Japanese Journal of Applied Physics, 2015, 54, 04DA04.	0.8	9
44	Structural Analyses of Thin SiO₂Films Formed by Thermal Oxidation of Atomically Flat Si Surface by Using Synchrotron Radiation X-Ray Characterization. ECS Journal of Solid State Science and Technology, 2015, 4, N96-N98.	0.9	5
45	Effect of Process Temperature of Al2O3 Atomic Layer Deposition Using Accurate Process Gasses Supply System. ECS Transactions, 2015, 66, 305-314.	0.3	1
46	Drastic suppression of the 1/f noise in MOSFETs: Fundamental fluctuations of mobility rather than induced mobility fluctuations. , 2015, , .		0
47	Flattening Technique of (551) Silicon Surface Using Xe/H2 Plasma. ECS Transactions, 2014, 61, 401-407.	0.3	1
48	High Selectivity in Dry Etching of Silicon Nitride over Si Using a Novel Hydrofluorocarbon Etch Gas in a Microwave Excited Plasma for FinFET. ECS Transactions, 2014, 61, 29-37.	0.3	3
49	Demonstrating individual leakage path from random telegraph signal of stress induced leakage current. , 2014, , .		1
50	Effect of Composition Ratio on Erbium Silicide Work Function on Different Morphology of Si(100) Surface Changed by Alkaline Etching. ECS Transactions, 2014, 61, 47-53.	0.3	0
51	Mass densification and defect restoration in chemical vapor deposition silicon dioxide film using Ar plasma excited by microwave. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2014, 32, 051502.	0.9	3
52	Extraction of time constants ratio over nine orders of magnitude for understanding random telegraph noise in metalâ€“oxideâ€“semiconductor field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC19.	0.8	13
53	Carrier mobility characteristics of (100), (110), and (551) oriented atomically flattened Si surfaces for fin structure design of multi-gate metalâ€“insulatorâ€“silicon field-effect transistors. Japanese Journal of Applied Physics, 2014, 53, 04EC04.	0.8	3
54	A novel analysis of oxide breakdown based on dynamic observation using ultra-high speed video capturing up to 10,000,000 frames per second. , 2014, , .		2

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55	Analyzing correlation between multiple traps in RTN characteristics. , 2014, , .		15
56	A statistical evaluation of effective time constants of random telegraph noise with various operation timings of in-pixel source follower transistors. Proceedings of SPIE, 2014, , .	0.8	1
57	Low-Interface-Trap-Density and High-Breakdown-Electric-Field SiN Films on GaN Formed by Plasma Pretreatment Using Microwave-Excited Plasma-Enhanced Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2013, 60, 1916-1922.	1.6	9
58	Stress induced leakage current generated by hot-hole injection. Microelectronic Engineering, 2013, 109, 298-301.	1.1	1
59	A Test Circuit for Extremely Low Gate Leakage Current Measurement of 10 aA for 80 000 MOSFETs in 80 s. IEEE Transactions on Semiconductor Manufacturing, 2013, 26, 288-295.	1.4	3
60	1/f Noise of accumulation mode p- and n-MOSFETs. , 2013, , .		2
61	A Statistical Evaluation of Random Telegraph Noise of In-Pixel Source Follower Equivalent Surface and Buried Channel Transistors. IEEE Transactions on Electron Devices, 2013, 60, 3555-3561.	1.6	25
62	Angle-resolved photoelectron spectroscopy study on interfacial transition layer and oxidation-induced residual stress in Si(100) substrate near the interface. Microelectronic Engineering, 2013, 109, 197-199.	1.1	1
63	High Integrity SiO2/Al2O3 Gate Stack for Normally-off GaN MOSFET. Materials Research Society Symposia Proceedings, 2013, 1561, 1.	0.1	0
64	Comprehensive Study on Chemical Structures of Compositional Transition Layer at SiO2/Si(100) Interface. ECS Transactions, 2013, 50, 313-318.	0.3	0
65	High Quality SiO₂/Al₂O₃ Gate Stack for GaN Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2013, 52, 04CF09.	0.8	37
66	Chemical Structure of Interfacial Transition Layer Formed on Si(100) and Its Dependence on Oxidation Temperature, Annealing in Forming Gas, and Difference in Oxidizing Species. Japanese Journal of Applied Physics, 2013, 52, 031302.	0.8	9
67	Effect of Erbium Silicide Crystallinity for Low Barrier Contact between Erbium Silicide and n-type Silicon. ECS Transactions, 2013, 50, 343-348.	0.3	0
68	Demonstrating distribution of SILC values at individual leakage spots. , 2013, , .		6
69	Schottky Barrier Height between Erbium Silicide and Various Morphology of Si(100) Surface Changed by Alkaline Etching. ECS Transactions, 2013, 58, 349-354.	0.3	0
70	High-speed and highly accurate evaluation of electrical characteristics in MOSFETs. , 2013, , .		4
71	The study of time constant analysis in random telegraph noise at the subthreshold voltage region. , 2013, , .		13
72	High Performance Normally-off GaN MOSFETs on Si Substrates. ECS Transactions, 2013, 58, 155-166.	0.3	2

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73	Effect of Composition Rate on Erbium Silicide Work Function on Different Silicon Surface Orientation. ECS Transactions, 2013, 53, 343-350.	0.3	0
74	XPS analysis of the terminatedâ€bonding states at GaN surface after chemical and plasma treatments. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1557-1560.	0.8	3
75	A statistical evaluation of low frequency noise of in-pixel source follower-equivalent transistors with various channel types and body bias. Proceedings of SPIE, 2013, , .	0.8	2
76	High Integrity SiO$_{2}$ Gate Insulator Formed by Microwave-Excited Plasma Enhanced Chemical Vapor Deposition for AlGaN/GaN Hybrid Metalâ€“Oxideâ€“Semiconductor Heterojunction Field-Effect Transistor on Si Substrate. Japanese Journal of Applied Physics, 2012, 51, 04DF03.	0.8	7
77	Electrical Properties of Silicon Nitride Using High Density and Low Plasma Damage PECVD Formed at 400ÂC. ECS Transactions, 2012, 45, 421-428.	0.3	3
78	Low Work Function between Erbium Silicide and n-type Silicon Controlled by Cap Film Stress. ECS Transactions, 2012, 45, 371-378.	0.3	0
79	Advanced Direct-Polishing Process Development of Non-Porous Ultralow-<i>k</i>Dielectric Fluorocarbon with Plasma Treatment on Cu Interconnects. Journal of the Electrochemical Society, 2012, 159, H407-H411.	1.3	5
80	On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01.	0.8	1
81	Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow-k Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03.	0.8	1
82	Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02.	0.8	4
83	Hole Mobility in Accumulation Mode Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DC07.	0.8	8
84	Influence of Forming Gas Annealing on SiO2/Si(100) Interface Structures Formed Utilizing Oxygen Molecules Different from that Utilizing Oxygen Radicals. ECS Transactions, 2012, 45, 453-460.	0.3	0
85	Statistical analysis of Random Telegraph Noise reduction effect by separating channel from the interface. , 2012, , .		25
86	A Simple Test Structure for Evaluating the Variability in Key Characteristics of a Large Number of MOSFETs. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 145-154.	1.4	5
87	A Test Circuit for Statistical Evaluation of $p-n$ Junction Leakage Current and its Noise. IEEE Transactions on Semiconductor Manufacturing, 2012, 25, 303-309.	1.4	3
88	A test circuit for extremely low gate leakage current measurement of 10 aA for 80,000 MOSFETs in 80 s. , 2012, , .		3
89	A novel chemically, thermally and electrically robust Cu interconnect structure with an organic non-porous ultralow-k dielectric fluorocarbon (k=2.2). , 2012, , .		1
90	The role of the temperature on the scattering mechanisms limiting the electron mobility in metal-oxide-semiconductor field-effect-transistors fabricated on (110) silicon-oriented wafers. , 2012, , .		4

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91	Densification of chemical vapor deposition silicon dioxide film using oxygen radical oxidation. Journal of Applied Physics, 2012, 111, 034101.	1.1	13
92	Cu Single Damascene Integration of an Organic Nonporous Ultralow- k Fluorocarbon Dielectric Deposited by Microwave-Excited Plasma-Enhanced CVD. IEEE Transactions on Electron Devices, 2012, 59, 1445-1453.	1.6	5
93	On the Interface Flattening Effect and Gate Insulator Breakdown Characteristic of Radical Reaction Based Insulator Formation Technology. Japanese Journal of Applied Physics, 2012, 51, 02BA01.	0.8	3
94	Recovery Characteristics of Anomalous Stress-Induced Leakage Current of 5.6 nm Oxide Films. Japanese Journal of Applied Physics, 2012, 51, 04DC02.	0.8	2
95	High Integrity SiO2Gate Insulator Formed by Microwave-Excited Plasma Enhanced Chemical Vapor Deposition for AlGaN/GaN Hybrid Metalâ€“Oxideâ€“Semiconductor Heterojunction Field-Effect Transistor on Si Substrate. Japanese Journal of Applied Physics, 2012, 51, 04DF03.	0.8	4
96	Hole Mobility in Accumulation Mode Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2012, 51, 04DC07.	0.8	2
97	Integration Process Development for Improved Compatibility with Organic Non-Porous Ultralow-<i>k</i>Dielectric Fluorocarbon on Advanced Cu Interconnects. Japanese Journal of Applied Physics, 2012, 51, 05EC03.	0.8	1
98	Formation speed of atomically flat surface on Si (100) in ultra-pure argon. Microelectronic Engineering, 2011, 88, 3133-3139.	1.1	14
99	Evaluation for Anomalous Stress-Induced Leakage Current of Gate $ hbox{SiO}_{2}$ Films Using Array Test Pattern. IEEE Transactions on Electron Devices, 2011, 58, 3307-3313.	1.6	8
100	High-Rate Deposition of Amorphous Silicon Films by Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2011, 50, 036502.	0.8	4
101	Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701.	0.8	21
102	Tribological Effects of Brush Scrubbing in Post Chemical Mechanical Planarization Cleaning on Electrical Characteristics in Novel Non-porous Low-kDielectric Fluorocarbon on Cu Interconnects. Japanese Journal of Applied Physics, 2011, 50, 05EC07.	0.8	9
103	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	0.8	4
104	Analysis of the Low-Frequency Noise Reduction in Si(100) Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC01.	0.8	6
105	Highly Reliable Radical SiO₂Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05.	0.8	5
106	Electrical Characteristics of Novel Non-porous Low-kDielectric Fluorocarbon on Cu Interconnects for 22 nm Generation and Beyond. Japanese Journal of Applied Physics, 2011, 50, 05EB02.	0.8	7
107	Tribological Study of Brush Scrubbing in Post-Chemical Mechanical Planarization Cleaning in Non-porous Ultralow-k Dielectricâˆ•Cu Interconnects. Journal of the Electrochemical Society, 2011, 158, H1145.	1.3	13
108	Cu damascene interconnects with an organic low-k fluorocarbon dielectric deposited by microwave excited plasma enhanced CVD. , 2011, , .		1

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109	(Invited) High Power Normally-Off GaN MOSFET. ECS Transactions, 2011, 41, 87-100.	0.3	4
110	Gate SiO2 Film Integrity on Ultra-Pure Argon Anneal (100) Silicon Surface. ECS Transactions, 2011, 41, 147-156.	0.3	6
111	Advanced Direct-Polish Process on Organic Non-Porous Ultra Low-k Fluorocarbon Dielectric on Cu Interconnects. ECS Transactions, 2011, 34, 653-658.	0.3	5
112	Visualization of Single Atomic Steps on An Ultra-Flat Si(100) Surface by Advanced Differential Interference Contrast Microscopy. Electrochemical and Solid-State Letters, 2011, 14, H351.	2.2	8
113	Understanding of traps causing random telegraph noise based on experimentally extracted time constants and amplitude. , 2011, , .		26
114	1/f CHANNEL NOISE AT HIGH DRAIN CURRENT IN MOS TRANSISTORS. Fluctuation and Noise Letters, 2011, 10, 431-445.	1.0	6
115	Different Properties of Erbium Silicides on Si(100) and Si(551) Orientation Surfaces. ECS Transactions, 2011, 41, 365-373.	0.3	0
116	Clear Difference between the Chemical Structure of SiO2/Si Interfaces Formed Using Oxygen Radicals versus Oxygen Molecules. ECS Transactions, 2011, 35, 115-122.	0.3	1
117	Pr3Si6N11/Si3N4 Stacked High-k Gate Dielectrics with High Quality Ultrathin Si3N4 Interfacial Layers. ECS Transactions, 2011, 35, 275-284.	0.3	1
118	High-Rate Deposition of Amorphous Silicon Films by Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2011, 50, 036502.	0.8	10
119	Analysis of the Low-Frequency Noise Reduction in Si(100) Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2011, 50, 04DC01.	0.8	3
120	Impact of Channel Direction Dependent Low Field Hole Mobility on (100) Orientation Silicon Surface. Japanese Journal of Applied Physics, 2011, 50, 04DC03.	0.8	5
121	Tribological Effects of Brush Scrubbing in Post Chemical Mechanical Planarization Cleaning on Electrical Characteristics in Novel Non-porous Low-<i>k</i>Dielectric Fluorocarbon on Cu Interconnects. Japanese Journal of Applied Physics, 2011, 50, 05EC07.	0.8	3
122	Large-Scale Test Circuits for High-Speed and Highly Accurate Evaluation of Variability and Noise in Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor Electrical Characteristics. Japanese Journal of Applied Physics, 2011, 50, 106701.	0.8	3
123	Highly Reliable Radical SiO₂Films on Atomically Flat Silicon Surface Formed by Low Temperature Pure Ar Annealing. Japanese Journal of Applied Physics, 2011, 50, 10PB05.	0.8	2
124	Mesoscopic-Scale and Small Strain Field beneath SiO2/Si Interface Revealed by a Multiple-Wave X-ray Diffraction Phenomenon - Depth of the Strain Field. E-Journal of Surface Science and Nanotechnology, 2011, 9, 47-50.	0.1	0
125	Electrical Characteristics of Novel Non-porous Low-kDielectric Fluorocarbon on Cu Interconnects for 22 nm Generation and Beyond. Japanese Journal of Applied Physics, 2011, 50, 05EB02.	0.8	1
126	Statistical Evaluation of Process Damage Using an Arrayed Test Pattern in a Large Number of MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 1310-1318.	1.6	12

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127	Relation Between the Mobility, $hbox{1}/f$ Noise, and Channel Direction in MOSFETs Fabricated on (100) and (110) Silicon-Oriented Wafers. IEEE Transactions on Electron Devices, 2010, 57, 1597-1607.	1.6	24
128	Characterization of MgZnO films grown by plasma enhanced metal-organic chemical vapor deposition. Thin Solid Films, 2010, 518, 2953-2956.	0.8	17
129	Modelling of the hole mobility in p-channel MOS transistors fabricated on (1 1 0) oriented silicon wafers. Solid-State Electronics, 2010, 54, 420-426.	0.8	18
130	Impact of Work Function Optimized S/D Silicide Contact for High Current Drivability CMOS. ECS Transactions, 2010, 28, 315-324.	0.3	2
131	Crystallographic orientation dependence of compositional transition and valence band offset at SiO2/Si interface formed using oxygen radicals. Applied Physics Letters, 2010, 96, 173103.	1.5	8
132	Ultra-low series resistance W/ErSi<inf>2</inf>/n⁺-Si and W/Pd<inf>2</inf>Si/p⁺-Si S/D electrodes for advanced CMOS platform. , 2010, , .		4
133	Atomically Flattening Technology at 850Â°C for Si(100) Surface. ECS Transactions, 2010, 28, 299-309.	0.3	28
134	Very High Performance CMOS on Si(551) Using Radical Oxidation Technology and Accumulation-Mode SOI Device Structure. Journal of the Electrochemical Society, 2010, 157, H389.	1.3	9
135	Evaluation of Narrow Gap Filling Ability in Shallow Trench Isolation by Organosiloxane Sol-Gel Precursor. ECS Transactions, 2010, 33, 135-143.	0.3	3
136	Low Contact Resistivity with Low Silicide/p+-Silicon Schottky Barrier for High-Performance p-Channel Metalâ€“Oxideâ€“Silicon Field Effect Transistors. Japanese Journal of Applied Physics, 2010, 49, 04DA03.	0.8	8
137	Experimental Investigation of Effect of Channel Doping Concentration on Random Telegraph Signal Noise. Japanese Journal of Applied Physics, 2010, 49, 04DC07.	0.8	19
138	Depth Profile of Nitrogen Atoms in Silicon Oxynitride Films Formed by Low-Electron-Temperature Microwave Plasma Nitridation. Japanese Journal of Applied Physics, 2010, 49, 091301.	0.8	8
139	Analysis of Hundreds of Time Constant Ratios and Amplitudes of Random Telegraph Signal with Very Large Scale Array Test Pattern. Japanese Journal of Applied Physics, 2010, 49, 04DC06.	0.8	12
140	End-Point Detection of Ta/TaN Chemical Mechanical Planarization via Forces Analysis. Japanese Journal of Applied Physics, 2010, 49, 05FC01.	0.8	20
141	Light-Emitting Diode Based on ZnO by Plasma-Enhanced Metalâ€“Organic Chemical Vapor Deposition Employing Microwave Excited Plasma. Japanese Journal of Applied Physics, 2010, 49, 04DG14.	0.8	5
142	A test structure for statistical evaluation of pn junction leakage current based on CMOS image sensor technology. , 2010, , .		3
143	Statistical evaluation of dynamic junction leakage current fluctuation using a simple arrayed capacitors circuit. , 2010, , .		3
144	Statistical evaluation for trap energy level of RTS characteristics. , 2010, , .		10

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145	Electrical Properties of Metal-Oxide-Containing SiO2Films Formed by Organosiloxane Solâ€"Gel Precursor. Japanese Journal of Applied Physics, 2010, 49, 111503.	0.8	1
146	Hole Mobility in Si(110) p-MOS Transistors. ECS Transactions, 2009, 16, 7-12.	0.3	1
147	In situObservation of Grain Growth on Electroplated Cu Film by Electron Backscatter Diffraction. Japanese Journal of Applied Physics, 2009, 48, 066507.	0.8	14
148	Impact of New Approach to Improve MOSFETs Performance with Ultrathin Gate Insulator. ECS Transactions, 2009, 19, 65-70.	0.3	0
149	Three-Step Room Temperature Wet Cleaning Process for Silicon Substrate. Solid State Phenomena, 2009, 145-146, 189-192.	0.3	1
150	Effect of Polisher Kinematics in Reducing Average and Variance of Shear Force and Increasing Removal Rate in Copper CMP. ECS Transactions, 2009, 18, 465-471.	0.3	0
151	Three-Step Room-Temperature Cleaning of Bare Silicon Surface for Radical-Reaction-Based Semiconductor Manufacturing. Journal of the Electrochemical Society, 2009, 156, H10.	1.3	8
152	Different Types of Degradation and Recovery Mechanisms on NBT Stress for Thin SIO2 Films by On-The-Fly Measurement. ECS Transactions, 2009, 19, 339-350.	0.3	0
153	Stress-induced leakage current and random telegraph signal. Journal of Vacuum Science & Technology B, 2009, 27, 435.	1.3	5
154	The electric properties of low-magnetic-loss magnetic composites containing Znâ€"Niâ€"Fe particles. Journal of Physics Condensed Matter, 2009, 21, 436009.	0.7	13
155	Complementary Metalâ€"Oxideâ€"Silicon Field-Effect-Transistors Featuring Atomically Flat Gate Insulator Film/Silicon Interface. Japanese Journal of Applied Physics, 2009, 48, 04C048.	0.8	28
156	Deposition of Microcrystalline Si1-xGexby RF Magnetron Sputtering on SiO2Substrates. Japanese Journal of Applied Physics, 2009, 48, 04C124.	0.8	1
157	Anomalous Random Telegraph Signal Extractions from a Very Large Number of n-Metal Oxide Semiconductor Field-Effect Transistors Using Test Element Groups with 0.47 Hzâ€"3.0 MHz Sampling Frequency. Japanese Journal of Applied Physics, 2009, 48, 04C044.	0.8	12
158	Effects of Ion-Bombardment-Assist and High Temperature on Growth of Zinc Oxide Films by Microwave Excited High Density Plasma Enhanced Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 04C135.	0.8	4
159	Different mechanism to explain the 1â^•f noise in n- and p-SOI-MOS transistors fabricated on (110) and (100) silicon-oriented wafers. Journal of Vacuum Science & Technology B, 2009, 27, 394-401.	1.3	13
160	Impact of Tungsten Capping Layer on Yttrium Silicide for Low-Resistance n+-Source/Drain Contacts. Japanese Journal of Applied Physics, 2009, 48, 04C046.	0.8	8
161	A Study on Very High Performance Novel Balanced Fully Depleted Silicon-on-Insulator Complementary Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors on Si(110) Using Accumulation-Mode Device Structure for Radio-Frequency Analog Circuits. Japanese Journal of Applied Physics, 2009, 48, 04C047.	0.8	1
162	Damage-Free Post-CMP Cleaning Solution for Low-<i>k</i> Fluorocarbon on Advanced Interconnects. Solid State Phenomena, 2009, 145-146, 381-384.	0.3	9

#	Article	IF	Citations
163	Effect of Additives in Organic Acid Solutions for Post-CMP Cleaning on Polymer Low-k Fluorocarbon. Journal of the Electrochemical Society, 2009, 156, H409.	1.3	26
164	Very High Performance CMOS on Si(551) Surface using Radical Oxidation Silicon Flattening Technology and Accumulation-mode SOI Device Structure. ECS Transactions, 2009, 25, 115-129.	0.3	4
165	Novel End-point Detection Method by Monitoring Shear Force Oscillation Frequency for Barrier Metal Polishing in Advanced LSI. Materials Research Society Symposia Proceedings, 2009, 1157, 1.	0.1	5
166	Reduction of Scratch on Brush Scrubbing in Post CMP Cleaning by Analyzing Contact Kinetics on Ultra Low-k Dielectric. ECS Transactions, 2009, 19, 103-109.	0.3	20
167	Low-Loss Composite Material Containing Fine Znâ€"Niâ€"Fe Flakes for High-Frequency Applications. IEEE Transactions on Magnetics, 2009, 45, 4337-4340.	1.2	18
168	Atomically Flat Silicon Surface and Silicon/Insulator Interface Formation Technologies for (100) Surface Orientation Large-Diameter Wafers Introducing High Performance and Low-Noise Metalâ€"Insulatorâ€"Silicon FETs. IEEE Transactions on Electron Devices, 2009, 56, 291-298.	1.6	59
169	Experimental demonstration and analysis of high performance and low 1/f noise Tri-gate MOSFETs by optimizing device structure. Microelectronic Engineering, 2009, 86, 1786-1788.	1.1	5
170	A Test Structure for Statistical Evaluation of Characteristics Variability in a Very Large Number of MOSFETs. , 2009, , .		12
171	Advanced Method for Measuring Ultra-Low Contact Resistivity Between Silicide and Silicon Based on Cross Bridge Kelvin Resistor. , 2009, , .		7
172	UV-Raman Spectroscopy Study on SiO2/Si Interface. ECS Transactions, 2009, 19, 55-66.	0.3	4
173	Accurate Time Constant of Random Telegraph Signal Extracted by a Sufficient Long Time Measurement in Very Large-Scale Array TEG. , 2009, , .		10
174	Damage free very low electron temperature plasma process for low Flicker noise in p-MOS fabricated on (100) and (110) silicon-oriented wafers. , 2009, , .		2
175	High-Frequency Propagation on Printed Circuit Board Using a Material With a Low Dielectric Constant, a Low Dielectric Loss, and a Flat Surface. IEEE Transactions on Components and Packaging Technologies, 2009, 32, 415-423.	1.4	7
176	Inductively coupled plasma generator for an environmentally benign perfluorocarbon abatement system. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2009, 27, 465-470.	0.9	4
177	Asymmetry of RTS characteristics along source-drain direction and statistical analysis of process-induced RTS. , 2009, , .		10
178	Characterization for High-Performance CMOS Using In-Wafer Advanced Kelvin-Contact Device Structure. IEEE Transactions on Semiconductor Manufacturing, 2009, 22, 126-133.	1.4	5
179	Data Analysis Technique of Atomic Force Microscopy for Atomically Flat Silicon Surfaces. IEICE Transactions on Electronics, 2009, E92-C, 664-670.	0.3	4
180	Accurate negative bias temperature instability lifetime prediction based on hole injection. Microelectronics Reliability, 2008, 48, 1649-1654.	0.9	4

#	Article	IF	Citations
181	Evaluation of Si3N4/Si interface by UV Raman spectroscopy. Applied Surface Science, 2008, 254, 6229-6231.	3.1	2
182	High Permeability and Low Loss Niâ€"Fe Composite Material for High-Frequency Applications. IEEE Transactions on Magnetics, 2008, 44, 2100-2106.	1.2	94
183	A new approach to realize high performance RF power FETs on Si(110) surface. Power Electronics Specialist Conference (PESC), IEEE, 2008, , .	0.0	1
184	New insulation material with flat-surface, low coefficient of thermal expansion, low-dielectric-loss for next generation semiconductor packages. , 2008, , .		2
185	High-Efficiency PFC Abatement System Utilizing Plasma Decomposition and Ca(OH)$_{2}$/CaO Immobilization. IEEE Transactions on Semiconductor Manufacturing, 2008, 21, 668-675.	1.4	8
186	Characterization of MOSFETs intrinsic performance using in-wafer advanced Kelvin-contact device structure for high performance CMOS LSIs. , 2008, , .		2
187	Statistical evaluation for anomalous SILC of tunnel oxide using integrated array TEG. , 2008, , .		5
188	Angle-resolved photoelectron study on the structures of silicon nitride films and Si3N4/Si interfaces formed using nitrogen-hydrogen radicals. Journal of Applied Physics, 2008, 104, .	1.1	14
189	Tantalum Nitride Sputtering Deposition with Xe on Fluorocarbon for Cu Interconnects. Journal of the Electrochemical Society, 2008, 155, H323.	1.3	1
190	High Performance Bottom Gate Î¼c-Si TFT Fabricated by Microwave Plasma CVD. Materials Research Society Symposia Proceedings, 2008, 1066, 1.	0.1	0
191	Characterization of Zinc Oxide Films Grown by a Newly Developed Plasma Enhanced Metal Organic Chemical Vapor Deposition Employing Microwave Excited High Density Plasma. Japanese Journal of Applied Physics, 2008, 47, 2994-2998.	0.8	6
192	Formation and Property of Yttrium and Yttrium Silicide Films as Low Schottcky Barrier material for n-Type Silicon. Japanese Journal of Applied Physics, 2008, 47, 3138.	0.8	14
193	Nitrogen Profile Study for SiON Gate Dielectrics of Advanced Dynamic Random Access Memory. Japanese Journal of Applied Physics, 2008, 47, 5380.	0.8	7
194	Performance Comparison of Ultrathin Fully Depleted Silicon-on-Insulator Inversion-, Intrinsic-, and Accumulation-Mode Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2008, 47, 2668-2671.	0.8	6
195	Low-Dielectric-Constant Nonporous Fluorocarbon Films for Interlayer Dielectric. Japanese Journal of Applied Physics, 2008, 47, 2515-2520.	0.8	18
196	Evaluation of New Amorphous Hydrocarbon Film for Copper Barrier Dielectric Film in Low-kCopper Metallization. Japanese Journal of Applied Physics, 2008, 47, 2531-2534.	0.8	0
197	Atomically flat gate insulator/silicon (100) interface formation introducing high mobility, ultra-low noise, and small characteristics variation CMOSFET. , 2008, , .		2
198	Damage-free microwave-excited plasma etching without carrier deactivation of heavily doped Si under thin silicide layer. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2008, 26, 8-16.	0.9	6

#	Article	IF	Citations
199	13.56 and 100 MHz Coupled Mode Rf-Sputtering for Ferroelectric Sr 2 (Ta 1 âˆ' x ,Nb x)2O 7 (STN) Film Applied to One-Transistor Type Ferroelectric Random Access Memory. Ferroelectrics, 2008, 368, 90-95.	0.3	0
200	Microcrystalline Si1-xGex Deposited by Magnetron Sputtering. ECS Transactions, 2008, 16, 183-192.	0.3	1
201	Development of Microwave-Excited Plasma-Enhanced Metalâ€"Organic Chemical Vapor Deposition System for Forming Ferroelectric Sr2(Ta1-x,Nbx)2O7Thin Film on Amorphous SiO2. Japanese Journal of Applied Physics, 2007, 46, 2200-2204.	0.8	1
202	The Influence of Interconnect Line Patterns using Flat-Surface and Low-Dielectric-Loss Material under High Speed Signal Propagation. , 2007, , .		8
203	Performance Boost Using a New Device Structure Design for SOI MOSFETs Beyond 25nm Node. ECS Transactions, 2007, 11, 349-355.	0.3	1
204	Statistical Analysis of RTS Noise and Low Frequency Noise in 1M MOSFETs Using an Advanced TEG. AIP Conference Proceedings, 2007, , .	0.3	3
205	Low Leakage Current and Low Resistivityp+nDiodes on Si(110) Fabricated by Ga+and B+Dual Ion Implantation for Low Temperature Sourceâ€"Drain Activation. Japanese Journal of Applied Physics, 2007, 46, 1848-1852.	0.8	0
206	Electric Characteristics of Si3N4Films Formed by Directly Radical Nitridation on Si(110) and Si(100) Surfaces. Japanese Journal of Applied Physics, 2007, 46, 1895-1898.	0.8	7
207	Very Low Bit Error Rate in Flash Memory Using Tunnel Dielectrics Formed by Kr/O2/NO Plasma Oxynitridation. Japanese Journal of Applied Physics, 2007, 46, 2148-2152.	0.8	17
208	New Statistical Evaluation Method for the Variation of Metalâ€"Oxideâ€"Semiconductor Field-Effect Transistors. Japanese Journal of Applied Physics, 2007, 46, 2054-2057.	0.8	27
209	Random Telegraph Signal Statistical Analysis using a Very Large-scale Array TEG with 1M MOSFETs. , 2007, , .		28
210	Subnitride and valence band offset at Si3N4âˆ•Si interface formed using nitrogen-hydrogen radicals. Applied Physics Letters, 2007, 90, 123114.	1.5	19
211	Impact of Improved Mobilities and Suppressed 1/f Noise in Fully Depleted SOI MOSFETs Fabricated on Si(110) Surface. ECS Transactions, 2007, 6, 101-106.	0.3	2
212	Hot Carrier Instability Mechanism in Accumulation-Mode Normally-off SOI nMOSFETs and Their Reliability Advantage. ECS Transactions, 2007, 6, 113-118.	0.3	7
213	Examination of degradation mechanism due to negative bias temperature stress from a perspective of hole energy for accurate lifetime prediction. Microelectronics Reliability, 2007, 47, 409-418.	0.9	4
214	Development of a Xenon recycling and supply system for plasma process. , 2007, , .		1
215	Modeling and Implementation of Subthreshold Characteristics of Accumulation-Mode MOSFETs for Various SOI Layer Thickness and Impurity Concentrations. SOI Conference, Proceedings of the IEEE International, 2007, , .	0.0	2
216	NBTI Mechanism Based on Hole-Injection for Accurate Lifetime Prediction. ECS Transactions, 2007, 6, 229-243.	0.3	4

#	Article	IF	Citations
217	Accurate Extraction of Conduction Parameter in MOSFETs on Si(110) surface. AIP Conference Proceedings, 2007, , .	0.3	2
218	High performance and highly reliable novel CMOS devices using accumulation mode multi-gate and fully depleted SOI MOSFETs. Microelectronic Engineering, 2007, 84, 2105-2108.	1.1	14
219	Circuit level prediction of device performance degradation due to negative bias temperature stress. Microelectronics Reliability, 2007, 47, 930-936.	0.9	4
220	Accuracy and Applicability of Low-Frequency Câ€“V Measurement Methods for Characterization of Ultrathin Gate Dielectrics With Large Current. IEEE Transactions on Electron Devices, 2007, 54, 1115-1124.	1.6	0
221	Very High Carrier Mobility for High-Performance CMOS on a Si(110) Surface. IEEE Transactions on Electron Devices, 2007, 54, 1438-1445.	1.6	70
222	Revolutional Progress of Silicon Technologies Exhibiting Very High Speed Performance Over a 50-GHz Clock Rate. IEEE Transactions on Electron Devices, 2007, 54, 1471-1477.	1.6	45
223	High quality gate insulator film formation on SiC using by microwave-excited high-density plasma. Microelectronics Reliability, 2007, 47, 786-789.	0.9	0
224	Formation of High Quality Silicon Nitride Films using Microwave Excitation Plasma. Shinku/Journal of the Vacuum Society of Japan, 2007, 50, 659-664.	0.2	0
225	X-ray Photoelectron Spectroscopic Study of Nitrogen Depth Profile in Radical Nitrided Silicon Oxynitride Film. Shinku/Journal of the Vacuum Society of Japan, 2007, 50, 672-677.	0.2	2
226	Impact of improved mobility and low flicker noise MOS transistors using accumulation mode fully depleted silicon-on-insulator devices. , 2006, , .		2
227	New era of silicon technologies due to radical reaction based semiconductor manufacturing. Journal Physics D: Applied Physics, 2006, 39, R1-R17.	1.3	88
228	X-ray photoelectron spectroscopy study of dielectric constant for Si compounds. Applied Physics Letters, 2006, 89, 154103.	1.5	8
229	Capacitanceâ€“Voltage Measurement Method for Ultrathin Gate Dielectrics Using LC Resonance Circuit. IEEE Transactions on Semiconductor Manufacturing, 2006, 19, 43-49.	1.4	6
230	1/f noise suppression of pMOSFETs fabricated on Si(100) and Si(110) using an alkali-free cleaning process. IEEE Transactions on Electron Devices, 2006, 53, 851-856.	1.6	44
231	Lattice Distortion at SiO2/Si(001) Interface Studied with High-Resolution Rutherford Backscattering Spectroscopy/Channeling. Japanese Journal of Applied Physics, 2006, 45, 2467-2469.	0.8	8
232	Fabrication of Pt/Sr2(Ta1-x,Nbx)2O7/IrO2/SiO2/Si Device with Large Memory Window and Metalâ€“Ferroelectricâ€“Metalâ€“Insulatorâ€“Si Field-Effect Transistor. Japanese Journal of Applied Physics, 2006, 45, 7336-7340.	0.8	0
233	Impact of Improved High-Performance Si(110)-Oriented Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistors Using Accumulation-Mode Fully Depleted Silicon-on-Insulator Devices. Japanese Journal of Applied Physics, 2006, 45, 3110-3116.	0.8	50
234	Relationship between Sr2(Ta1-x,Nbx)2O7Crystal Phase and RF-Sputtering Plasma Condition for Metalâ€“Ferroelectricâ€“Insulatorâ€“Si Structure Device Formation. Japanese Journal of Applied Physics, 2006, 45, 3207-3212.	0.8	3

#	Article	IF	Citations
235	Control of Nitrogen Depth Profile near Silicon Oxynitride/Si(100) Interface Formed by Radical Nitridation. Japanese Journal of Applied Physics, 2006, 45, 6203-6209.	0.8	3
236	Accurate Circuit Performance Prediction Model and Lifetime Prediction Method of NBT Stressed Devices for Highly Reliable ULSI Circuits. , 2006, , .		3
237	LOW VOLTAGE 3 V OPERATION OF FERROELECTRIC MULTI-LAYER STACK MFIS STRUCTURE DEVICE FORMED BY PLASMA PHYSICAL VAPOR DEPOSITION AND OXYGEN RADICAL TREATMENT. Integrated Ferroelectrics, 2006, 81, 47-55.	0.3	0
238	Adsorption Behavior of Various Fluorocarbon Gases on Silicon Wafer Surface. Japanese Journal of Applied Physics, 2005, 44, 2245-2251.	0.8	0
239	Impact of interface micro-roughness on low frequency noise in (110) and (100) pMOSFETs. AIP Conference Proceedings, 2005, , .	0.3	1
240	Hydrogen termination of Si(110) surfaces upon wet cleaning revealed by highly resolved scanning tunneling microscopy. Journal of Applied Physics, 2005, 98, 103525.	1.1	22
241	Control of Nitrogen Depth Profile and Chemical Bonding State in Silicon Oxynitride Films Formed by Radical Nitridation. Japanese Journal of Applied Physics, 2005, 44, 7395-7399.	0.8	4
242	GEOMETRY AND BIAS DEPENDENCE OF LOW-FREQUENCY RANDOM TELEGRAPH SIGNAL AND 1/f NOISE LEVELS IN MOSFETS. Fluctuation and Noise Letters, 2005, 05, L539-L548.	1.0	19
243	XPS Study of H-Terminated Silicon Surface under Inert Gas and UHV Annealing. Journal of the Electrochemical Society, 2005, 152, G163.	1.3	21
244	A Low-Dielectric-Constant Sr2(Ta1-x,Nbx)2O7Thin Film Controlling the Crystal Orientation on an IrO2Substrate for One-Transistor-Type Ferroelectric Memory Device. Japanese Journal of Applied Physics, 2004, 43, 2194-2198.	0.8	3
245	High-Speed Damage-Free Contact Hole Etching Using Dual Shower Head Microwave-Excited High-Density-Plasma Equipment. Japanese Journal of Applied Physics, 2004, 43, 1784-1787.	0.8	34
246	MFIS Structure Device with a Low Dielectric Constant Ferroelectric Sr2(Ta1â^'x,Nbx)2O7 Formed by Plasma Physical Vapor Deposition and Oxygen Radical Treatment. Integrated Ferroelectrics, 2004, 65, 29-38.	0.3	2
247	Accurate Temperature Drift model of MOSFETs Mobility for Analog Circuits. , 2004, , 291-294.		0
248	Reliability of silicon nitride gate dielectrics grown at 400 Â°C formed by microwave-excited high-density plasma. Applied Surface Science, 2003, 216, 246-251.	3.1	3
249	Oxygen radical treatment applied to ferroelectric thin films. Applied Surface Science, 2003, 216, 239-245.	3.1	3
250	High-Quality Silicon Oxide Film Formed by Diffusion Region Plasma Enhanced Chemical Vapor Deposition and Oxygen Radical Treatment Using Microwave-Excited High-Density Plasma. Japanese Journal of Applied Physics, 2003, 42, 1911-1915.	0.8	31
251	A Technology for Reducing Flicker Noise for ULSI Applications. Japanese Journal of Applied Physics, 2003, 42, 2106-2109.	0.8	23
252	Ferroelectric Sr2(Ta1-x, Nbx)2O7with a Low Dielectric Constant by Plasma Physical Vapor Deposition and Oxygen Radical Treatment. Japanese Journal of Applied Physics, 2003, 42, 2050-2054.	0.8	6

#	Article	IF	Citations
253	Saturation Phenomenon of Stress-Induced Gate Leakage Current. Japanese Journal of Applied Physics, 2002, 41, 2335-2338.	0.8	3
254	Title is missing!. Journal of the Japan Society for Precision Engineering, 2002, 68, 1144-1149.	0.0	0
255	Time-dependent dielectric breakdown of SiO2 films in a wide electric field range. Microelectronics Reliability, 2001, 41, 47-52.	0.9	16
256	Simulation of Dopant Redistribution During Gate Oxidation Including Transient-Enhanced Diffusion Caused by Implantation Damage. Japanese Journal of Applied Physics, 2000, 39, 2565-2576.	0.8	1
257	Precise Control of Nitrogen Profiles and Nitrogen Bond States for Highly Reliable N[sub 2]O-Grown Oxynitride. Journal of the Electrochemical Society, 2000, 147, 1888.	1.3	12
258	Angle resolved X-ray photoelectron spectroscopic study of ultrathin oxynitrides. Materials Science in Semiconductor Processing, 1999, 2, 225-231.	1.9	15
259	Origin of positive charge generated in thin SiO/sub 2/ films during high-field electrical stress. IEEE Transactions on Electron Devices, 1999, 46, 947-953.	1.6	18
260	Effects of N distribution on charge trapping and TDDB characteristics of N/sub 2/O annealed wet oxide. IEEE Transactions on Electron Devices, 1999, 46, 1121-1126.	1.6	12
261	High Performance 0.2 Âµm Dual Gate Complementary MOS Technologies by Suppression of Transient-Enhanced-Diffusion using Rapid Thermal Annealing. Japanese Journal of Applied Physics, 1998, 37, 1054-1058.	0.8	3
262	Highly Reliable SiO2Films Formed by UV-O2Oxidation. Japanese Journal of Applied Physics, 1998, 37, 1122-1124.	0.8	12
263	Dielectric breakdown caused by hole-induced-defect in thin SiO2 films. Applied Surface Science, 1997, 117-118, 245-248.	3.1	7
264	Electron Traps and Excess Current Induced by Hotâ€Hole Injection into Thin SiO2 Films. Journal of the Electrochemical Society, 1996, 143, 3377-3383.	1.3	24
265	Clarification of Nitridation Effect on Oxide Formation Methods. Japanese Journal of Applied Physics, 1996, 35, 1454-1459.	0.8	7
266	Charge Transport in Ultrathin Silicon Nitrides. Journal of the Electrochemical Society, 1995, 142, 990-996.	1.3	11
267	Model for the substrate hole current based on thermionic hole emission from the anode during Fowlerâ€"Nordheim electron tunneling innâ€channel metalâ€oxideâ€semiconductor fieldâ€effect transistors. Journal of Applied Physics, 1995, 77, 3277-3282.	1.1	53
268	Preoxide-Controlled Oxidation for Very Thin Oxide Films. Japanese Journal of Applied Physics, 1993, 32, 294-297.	0.8	21
269	Effect of Silicon WaferIn SituCleaning on the Chemical Structure of Ultrathin Silicon Oxide Film. Japanese Journal of Applied Physics, 1991, 30, 3584-3589.	0.8	15
270	Native Oxide Growth on Silicon Surface in Ultrapure Water and Hydrogen Peroxide. Japanese Journal of Applied Physics, 1990, 29, L2392-L2394.	0.8	33

#	Article	IF	Citations
271	1/f noise degradation caused by Fowler-Nordheim tunneling stress in MOSFETs. , 0, , .		0
272	Effect of Various Cleaning Solutions and Brush Scrubber Kinematics on the Frictional Attributes of Post Copper CMP Cleaning Process. Solid State Phenomena, 0, 145-146, 363-366.	0.3	8
273	New Processes and Technologies to Reduce the Lowâ€Frequency Noise of Digital and Analog Circuits. , 0, , .		0
274	Carrier Mobility in Field-Effect Transistors. , 0, , .		2